IN THE CLAIMS:

Please amend claims 16-20 as follows. A detailed listing of all claims is as follows.

Claim 1 (Withdrawn): A method of crystallizing amorphous silicon, comprising:

forming an amorphous silicon layer on a substrate;

placing a mask over the substrate including the amorphous silicon layer; and

applying a laser beam onto the amorphous silicon layer through the mask to form a first crystallized region, the laser beam having an energy intensity high enough to completely melt the amorphous silicon layer, wherein the mask comprises,

a base substrate,

a phase shift layer on the base substrate, having a plurality of first stripes having a first width separated by slits, and

a blocking layer overlapping the phase shift layer, having a plurality of second stripes having a second width narrower than the first width, the second stripes being parallel to the first stripes.

Claim 2 (Withdrawn): The method according to claim 1, wherein the base substrate has a high heat resistance.

Claim 3 (Withdrawn): The method according to claim 2, wherein the base substrate is quartz.

Claim 4 (Withdrawn): The method according to claim 1, wherein the phase shift layer is molybdenum silicide ($MoSi_x$).

Claim 5 (Withdrawn): The method according to claim 1, wherein the blocking layer is capable of reflecting a laser beam.

Claim 6 (Withdrawn): The method according to claim 5, wherein the blocking layer is chromium (Cr).

Claim 7 (Withdrawn): The method according to claim 1, wherein each of the slits has a width in a range of about 1 to 3 micrometers (□).

Claim 8 (Withdrawn): The method according to claim 1, wherein the first width is in a range of about 1 to 3 micrometers (□).

Claim 9 (Withdrawn): The method according to claim 1, wherein the first width is substantially the same as a width of each slit.

Claim 10 (Withdrawn): The method according to claim 1, wherein each of the second stripes of the blocking layer is disposed over the middle of each of the first stripes of the phase shift layer, thereby exposing both sides of each first stripe.

Claim 11 (Withdrawn): The method according to claim 1, wherein the first crystallized region is formed by two laser shots, and the first width and a width of each slit are about 2 micrometers (□).

Claim 12 (Withdrawn): The method according to claim 1, wherein the phase shift layer has exposed portions to the laser beam, so that the laser beam passes through the mask has a reversed profile at an energy intensity higher than a melting point of silicon.

Claim 13 (Withdrawn): The method according to claim 1, wherein the applying a laser beam is performed by an eximer laser.

Claim 14 (Original): A mask for crystallizing amorphous silicon, comprising:

a base substrate;

a phase shift layer on the base substrate, having a plurality of first stripes having a first width separated by slits; and

a blocking layer overlapping the phase shift layer, having a plurality of second stripes having a second width narrower than the first width, the second stripes being parallel to the first stripes.

Claim 15 (Original): The mask according to claim 14, wherein the phase shift layer is capable of reversing a phase of light.

Claim 16 (Currently Amended): The mask according to claim 15, wherein the phase shift layer is formed of molybdenum silicide (MoSix).

Claim 17 (Currently Amended): The mask according to claim 14, wherein the blocking layer is capable of reflecting a laser beam.

Claim 18 (Currently Amended): The mask according to claim 17, wherein the blocking layer is formed of chromium (Cr).

Claim 19 (Currently Amended): The mask according to claim 14, wherein each of the slits has a width within a range of about 1 to 3 micrometers [[(□)]] (μm).

Claim 20 (Currently Amended): The mask according to claim 14, wherein the first width is in the range of about 1 to 3 micrometers [[(□)]] (μm).

Claim 21 (Original): The mask according to claim 14, wherein each of the second stripes of the blocking layer is disposed over the middle of each of the first stripes of the phase shift layer, thereby exposing both sides of each first stripe.

Claim 22 (Original): The mask according to claim 14, wherein the first width is smaller than or equal to a width of each slit.